

R-C Thermal Model Parameters

DESCRIPTION

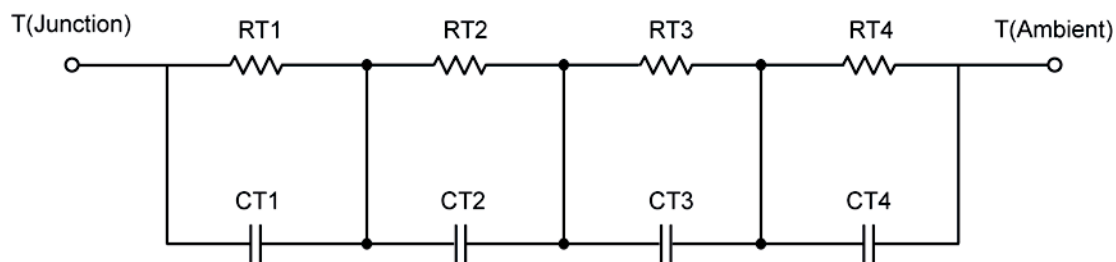
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	12.6804	N/A	6.4948
RT2	22.4830	N/A	19.9734
RT3	35.0832	N/A	11.0076
RT4	54.7534	N/A	7.5242
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	331.6698 u	N/A	146.2618 m
CT2	65.7997 m	N/A	1.7629 m
CT3	3.2601 m	N/A	6.0938 m
CT4	1.3907	N/A	204.0468 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	16.0369	N/A	8.8277
RF2	36.7018	N/A	29.5212
RF3	20.6292	N/A	2.1524
RF4	51.6321	N/A	4.4987
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	313.7956 u	N/A	154.9639 u
CF2	3.1498 m	N/A	1.2167 m
CF3	83.2244 m	N/A	122.3759 m
CF4	1.4111	N/A	657.6034 u

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

